

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

GT10J311

HIGH POWER SWITCHING APPLICATIONS

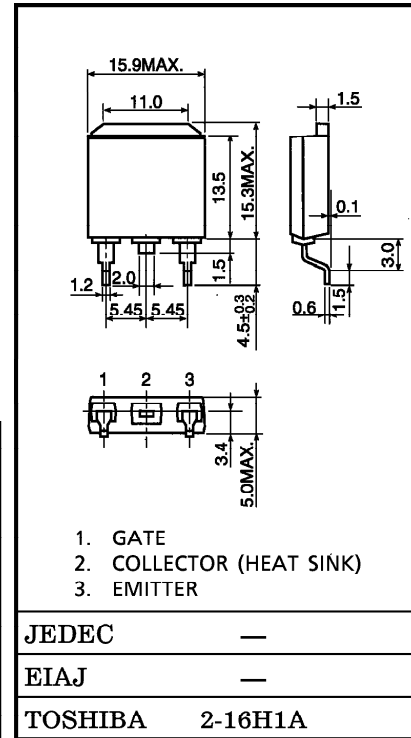
MOTOR CONTROL APPLICATIONS

- The 3rd Generation
- Enhancement-Mode
- High Speed : $t_f=0.30\mu s$ (Max.)
- Low Saturation Voltage : $V_{CE(sat)}=2.7V$ (Max.)
- FRD included between Emitter and Collector

MAXIMUM RATINGS ($T_a = 25^\circ C$)

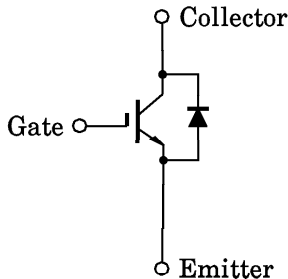
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Emitter Voltage	V_{CES}	600	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	DC	I_C 10	A
	1ms	I_{CP} 20	A
Emitter-Collector Forward Current	DC	I_F 10	A
	1ms	I_{FM} 20	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	80	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

Unit in mm



Weight : 3.65g

EQUIVALENT CIRCUIT



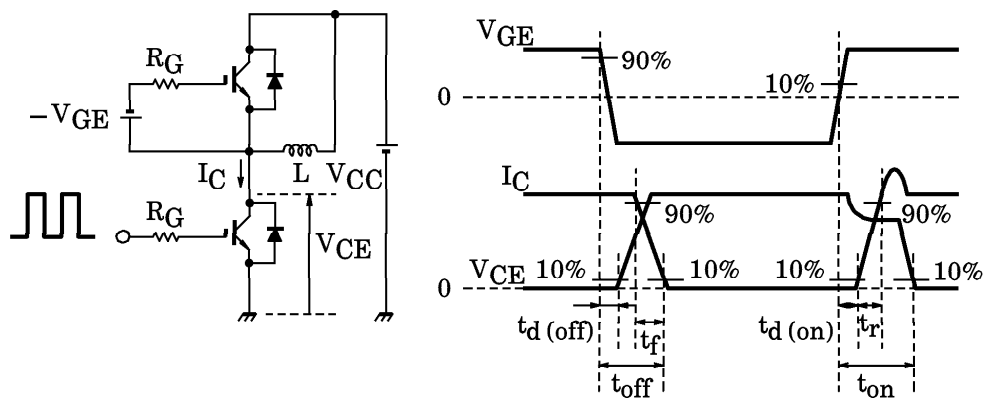
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	500	nA
Collector Cut-Off Current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emmitter Cut-Off Voltage	$V_{GE(OFF)}$	$I_C = 1mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emmitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, V_{GE} = 15V$	—	2.1	2.7	V
Input Capacitance	C_{ies}	$V_{CE} = 20V, V_{GE} = 0, f = 1MHz$	—	720	—	pF
Switching Time	Rise Time	Inductive Load $V_{CC} = 300V, I_C = 10A$ $V_{GG} = \pm 15V, R_G = 100\Omega$ (Note)	—	0.12	—	μs
	Turn-On Time		—	0.40	—	
	Fall Time		—	0.15	0.30	
	Turn-Off Time		—	0.50	—	
Peak Forward Voltage	V_F	$I_F = 10A, V_{GE} = 0$	—	—	2.0	V
Reverse Recovery Time	t_{rr}	$I_F = 10A, di/dt = -100A/\mu s$	—	—	200	ns
Thermal Resistance (IGBT)	$R_{th(j-c)}$	—	—	—	1.56	°C/W
Thermal Resistance (Diode)	$R_{th(j-c)}$	—	—	—	3.13	°C/W

(Note) Switching time measurement circuit and input/output waveforms



Switching loss measurement waveforms

